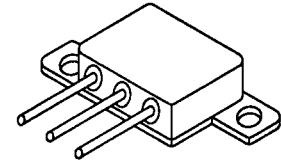
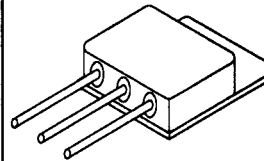




PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**Designer's Data Sheet****FEATURES:**

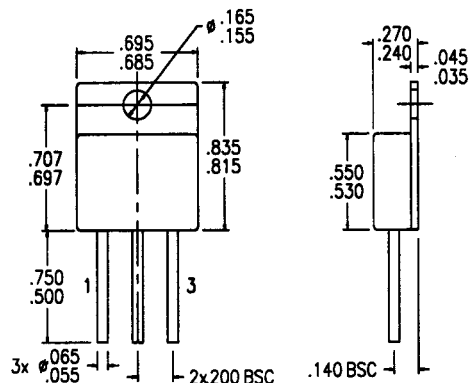
- Rugged construction with polysilicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Ceramic Seals for improved hermeticity
- Hermetically sealed power package
- TX, TXV and Space Level screening available
- Replaces: IXTH11N80 Types

SFF11N80N
SFF11N80P**11 AMPS**
800 VOLTS
0.95Ω
N-CHANNEL
POWER MOSFET**TO-258****TO-259****MAXIMUM RATINGS**

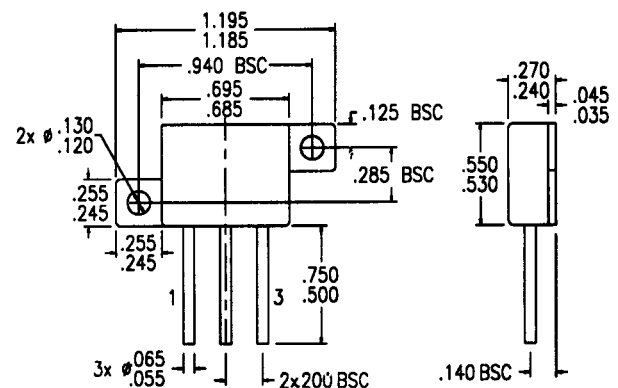
CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	800	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	11	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +175	°C
Thermal Resistance, Junction to Case	R _{θJC}	0.83	°C/W
Total Device Dissipation @ TC=25°C	P _D	150	Watts
Total Device Dissipation @ TC=55°C		114	

PACKAGE OUTLINE: TO-258 (N)

PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE

**PACKAGE OUTLINE: TO-259 (P)**

PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00217 A**MED**

SFF11N80N SFF11N80P

PRELIMINARY



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ELECTRICAL CHARACTERISTICS @ T_J=25 °C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)		BV _{DSS}	800	---	---	V
Drain to Source on State Resistance (V _{GS} =10 V, I _D =50% Rated ID)		R _{DS(on)}	---	---	0.95	Ω
On State Drain Current (V _{DS} > I _{D(on)} X R _{DS(on)} Max, V _{GS} =10 V)		I _{D(on)}	11	---	---	A
Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =250μA)		V _{GS(th)}	2.0	---	4.5	V
Forward Transconductance (V _{DS} > I _{D(on)} X R _{DS(on)} Max, I _{DS} =50% rated ID)		g _{fs}	8.0	14	---	S(Ω)
Zero Gate Voltage Drain Current (V _{DS} =max rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125°C)		I _{DSS}	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS}	I _{GSS}	---	---	+100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 80% rated V _{DS} 50% Rated ID	Q _g Q _{gs} Q _{gd}	---	128 30 55	155 45 80	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _{DD} =50% rated V _{DS} 50% rated I _D R _G =2.0Ω	t _{d(on)} t _r t _{d(off)} t _f	---	20 33 63 32	50 50 100 50	nsec
Diode Forward Voltage (I _S =rated ID, V _{GS} =0 V, T _J =25°C)		V _{SD}	---	---	1.5	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =rated ID di/dt=100 A/μsec	t _{rr} Q _{RR}	---	---	250 ---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _{DS} =25 Volts f= 1 MHz	C _{iss} C _{oss} C _{rss}	---	4200 360 100	---	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.